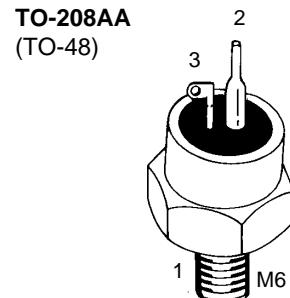
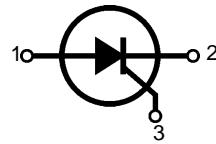


Phase Control Thyristors

V_{RRM} = 800-1600 V
I_{T(RMS)} = 50 A
I_{T(AV)M} = 32 A

V _{RSM} V _{DSM}	V _{RRM} V _{DRM}	Type
V	V	
900	800	CS 23-08io2
1300	1200	CS 23-12io2
1700	1600	CS 23-16io2



1 = Anode, 2 = Cathode, 3 = Gate

Symbol	Test Conditions	Maximum Ratings	
I _{T(RMS)}	T _{VJ} = T _{VJM}	50	A
I _{T(AV)M}	T _{case} = 85°C; 180° sine	25	A
	T _{case} = 69°C; 180° sine	32	A
I _{TSM}	T _{VJ} = 45°C; V _R = 0	450	A
	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	480	A
	T _{VJ} = T _{VJM} V _R = 0	400	A
	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	430	A
I ² t	T _{VJ} = 45°C V _R = 0	1010	A ² s
	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	970	A ² s
	T _{VJ} = T _{VJM} V _R = 0	800	A ² s
	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	770	A ² s
(di/dt) _{cr}	T _{VJ} = T _{VJM} f = 50Hz, t _p = 200 μs V _D = 2/3 V _{DRM} I _G = 0.3 A di _G /dt = 0.3 A/μs	150	A/μs
	repetitive, I _T = 75 A		
	non repetitive, I _T = I _{T(AV)M}	500	A/μs
(dv/dt) _{cr}	T _{VJ} = T _{VJM} ; R _{GR} = ∞; method 1 (linear voltage rise)	1000	V/μs
P _{GM}	T _{VJ} = T _{VJM} I _T = I _{T(AV)M}	10	W
	t _p = 30 μs	5	W
	t _p = 300 μs	0.5	W
P _{G(AV)}			
V _{RGM}		10	V
T _{VJ}		-40...+125	°C
T _{VJM}		125	°C
T _{stg}		-40...+125	°C
M _d	Mounting torque	2.7-3.3 24-29	Nm lb.in.
Weight		12	g

Data according to IEC 60747
 IXYS reserves the right to change limits, test conditions and dimensions

Features

- Thyristor for line frequencies
- International standard package JEDEC TO-208AA
- Planar glassivated chip
- Long-term stability of blocking currents and voltages

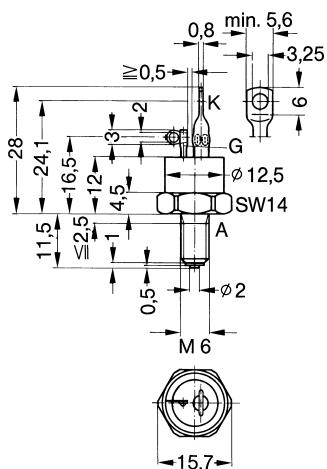
Applications

- Motor control
- Power converter
- AC power controller

Advantages

- Space and weight savings
- Simple mounting
- Improved temperature and power cycling

Dimensions in mm (1 mm = 0.0394")



Symbol	Test Conditions	Characteristic Values		
I_R, I_D	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	\leq	3	mA
V_T	$I_T = 80 \text{ A}; T_{VJ} = 25^\circ\text{C}$	\leq	1.8	V
V_{TO}	For power-loss calculations only ($T_{VJ} = 125^\circ\text{C}$)	1.0	V	
r_T		10	$\text{m}\Omega$	
V_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	\leq	2.5	V
I_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	\leq	50	mA
I_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	\leq	0.2	V
I_{GD}		\leq	1	mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}$ $I_G = 0.15 \text{ A}; di_G/dt = 0.15 \text{ A}/\mu\text{s}$	\leq	200	mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	\leq	100	mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.15 \text{ A}; di_G/dt = 0.15 \text{ A}/\mu\text{s}$	\leq	2	μs
t_q	$T_{VJ} = T_{VJM}; I_T = 25 \text{ A}, t_p = 300 \mu\text{s}; di/dt = -20 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}; dv/dt = 20 \text{ V}/\mu\text{s}; V_D = 2/3 V_{DRM}$	typ.	60	μs
R_{thJC}	DC current	1.0	K/W	
R_{thJH}	DC current	1.61	K/W	
d_s	Creepage distance on surface	1.5	mm	
d_A	Strike distance through air	1.5	mm	
a	Max. acceleration, 50 Hz	50	m/s^2	

Accessories:

Nut M6 DIN 439/SW14

Lock washer A6 DIN 128

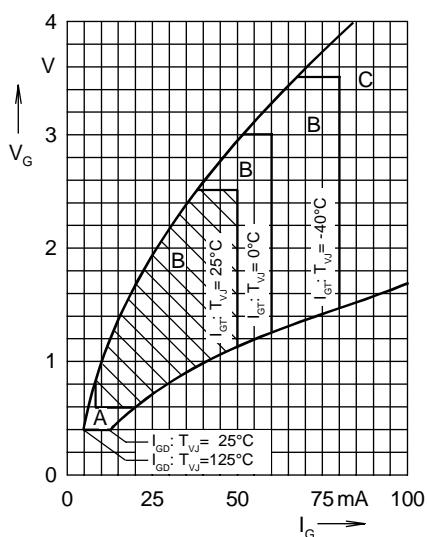
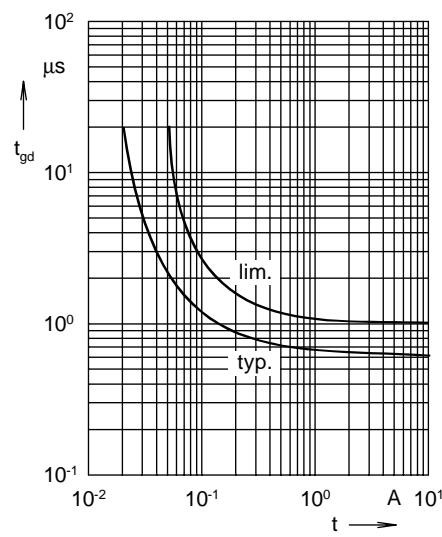
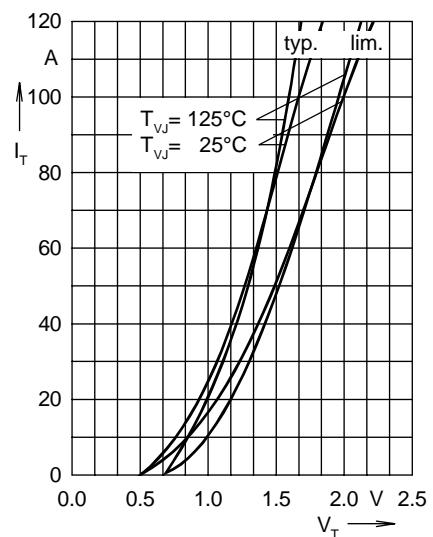
Fig. 1 Gate voltage and gate current
Triggering:
A = no; B = possible; C = safeFig. 2 Gate controlled delay time t_{gd} 

Fig. 3 On-state characteristics

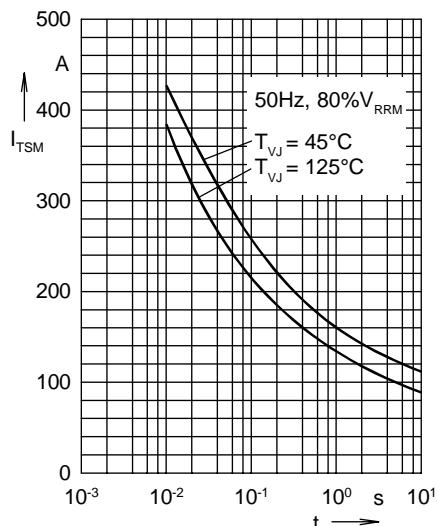


Fig. 4 Surge overload current
 I_{TSM} : crest value, t: duration

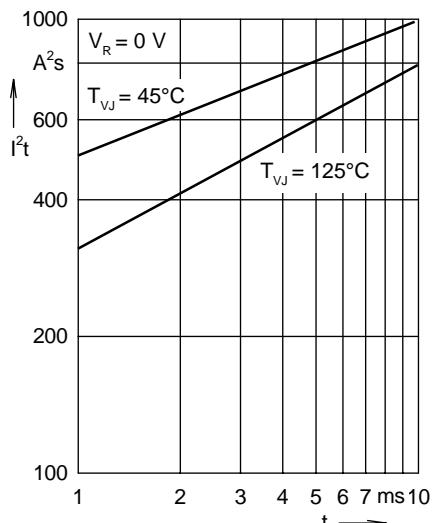


Fig. 5 I^2t versus time (1-10 ms)

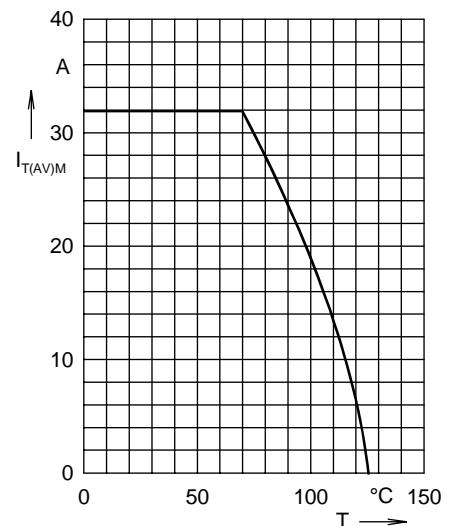


Fig. 6 Maximum forward current at case temperature 180° sine

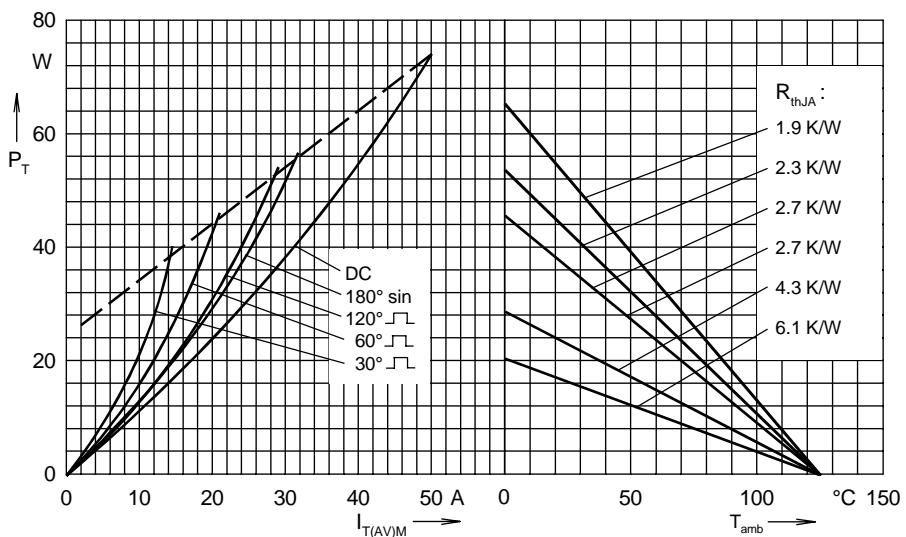


Fig. 7 Power dissipation versus on-state current and ambient temperature

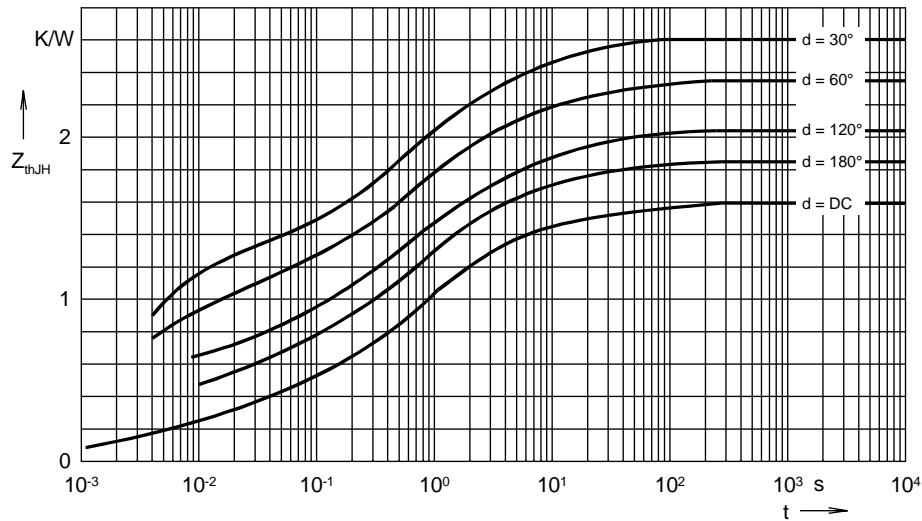


Fig. 8 Transient thermal impedance junction to heatsink

R_{thJH} for various conduction angles d:

d	R_{thJH} (K/W)
DC	1.61
180°	1.85
120°	2.03
60°	2.35
30°	2.60

Constants for Z_{thJH} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.224	0.003
2	0.132	0.028
3	0.321	0.216
4	0.522	1.1
5	0.249	4.2
6	0.162	43.2